

B2 22. (amended) A semiconductor device manufactured by a wire bonding method using a metal wire, comprising a region adapted to be contacted by a probe needle for inspection brought into contact therewith, and a region in which a metal ball formed at a tip of said metal wire by electric discharge is bonded to a terminal electrode formed on the semiconductor device.

23. (amended) The semiconductor device according to claim 22, wherein said terminal electrode is formed on an element or wiring inside said semiconductor device.

Please add new claim 24 as follows.

B3 24. (new) The semiconductor device according to claim 22, wherein a shape of the terminal electrode is rectangular, the shape having a portion protruded from a square that surrounds the region wherein the metal ball is bonded to the terminal electrode, the protruded portion being the region adapted to be contacted by the probe needle.